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(54) **SEMICONDUCTOR STRUCTURE AND METHOD OF MAKING THE SAME**

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ABSTRACT

A semiconductor structure and a preparation method making it are disclosed. The semiconductor structure includes: a substrate, a bit line contact structure, a first epitaxial layer, a bit line and a second epitaxial layer. The structure includes bit line contact holes. The bit line contact structure is disposed in one of the bit line contact holes. The first epitaxial layer is epitaxially grown on the sidewalls of the bit line contact structure. The bit line includes a connection layer connected to the bit line contact structure. The second epitaxial layer is epitaxially grown on the sidewalls of the connection layer. The present disclosure can reduce the contact resistance and parasitic capacitance between the bit line contact structures and the bit lines, thereby improving the electrical performance of the semiconductor structure, thereby raising the reliability and yield of the semiconductor structure.

